

General Description

The AGM403A1-M1 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

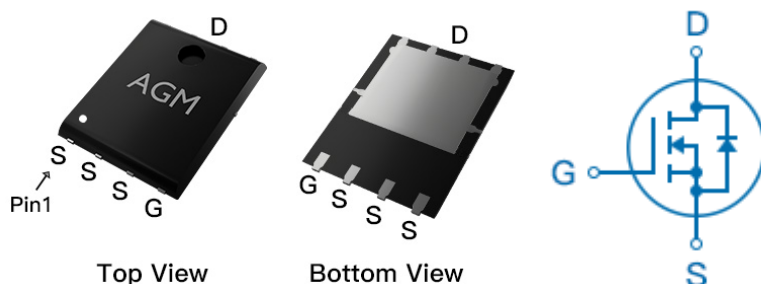
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
40V	2.2mΩ	100A

PDFN5*6 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM403A1	AGM403A1-M1	PDFN5*6	330mm	12mm	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	40	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	100	A
	Drain Current-Continuous(Tc=100°C)	67	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	400	A
PD	Maximum Power Dissipation(Tc=25°C)	62.5	w
	Maximum Power Dissipation(Tc=100°C)	25	w
EAS	Avalanche energy (Note 3)	400	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	20	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	2.0	°C/W

Table 3. Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	40	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=40V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	1.6	2.2	V
gFS	Forward Transconductance	VDS=5V,ID=10A	--	36	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=20A	--	2.2	4.0	mΩ
		VGS=4.5V, ID=10A	--	3.2	6.0	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=15V,VGS=0V, F=1MHZ	--	5341	--	pF
Coss	Output Capacitance		--	380	--	pF
Crss	Reverse Transfer Capacitance		--	293	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	0.9	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=20V, ID=30A,RGEN=3Ω	--	12	--	nS
tr	Turn-on Rise Time		--	16	--	nS
td(off)	Turn-Off Delay Time		--	39	--	nS
tf	Turn-Off Fall Time		--	15	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=20V, ID=30A	--	65	--	nC
Qgs	Gate-Source Charge		--	12.5	--	nC
Qgd	Gate-Drain Charge		--	15	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	100	A
VSD	Forward on Voltage	VGS=0V,IS=20A	--	--	1.2	V
trr	Reverse Recovery Time	IF=20A , dI/dt=100A/μs , TJ=25℃	--	22	--	ns
Qrr	Reverse Recovery Charge		--	11	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T_J=25°C , V_{DD}=25V, V_{gs}=10V, I_D=40A, L=0.5mH, R_G=25ohm

Typical Performance Characteristics

Figure 1: Output Characteristics

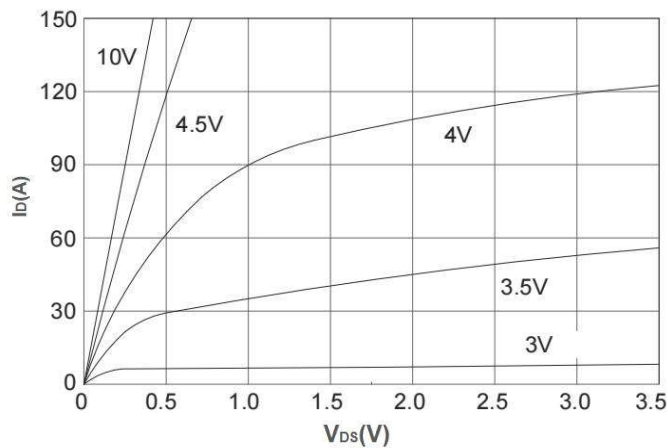


Figure 2: Typical Transfer Characteristics

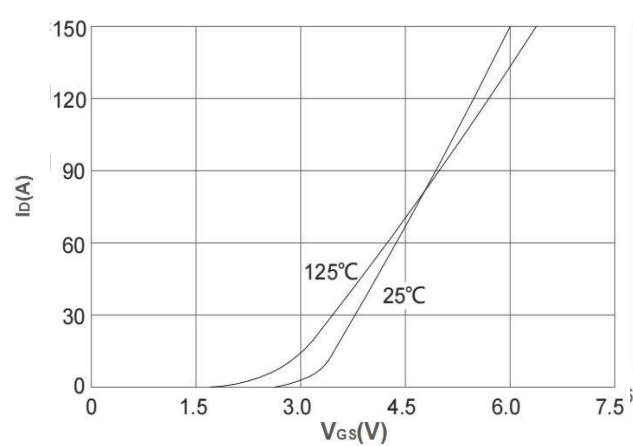


Figure 3: On-resistance vs. Drain Current

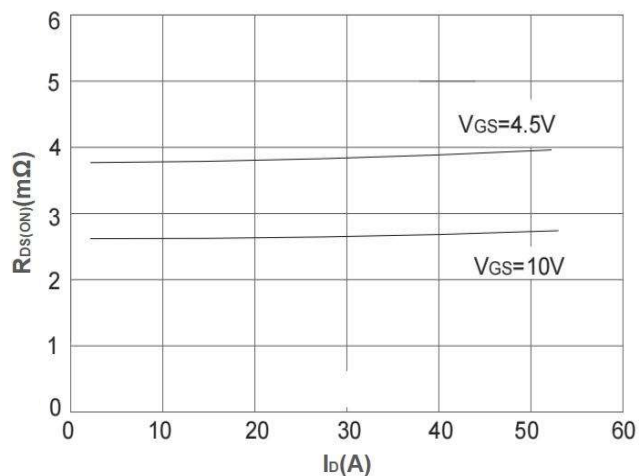


Figure 4: Body Diode Characteristics

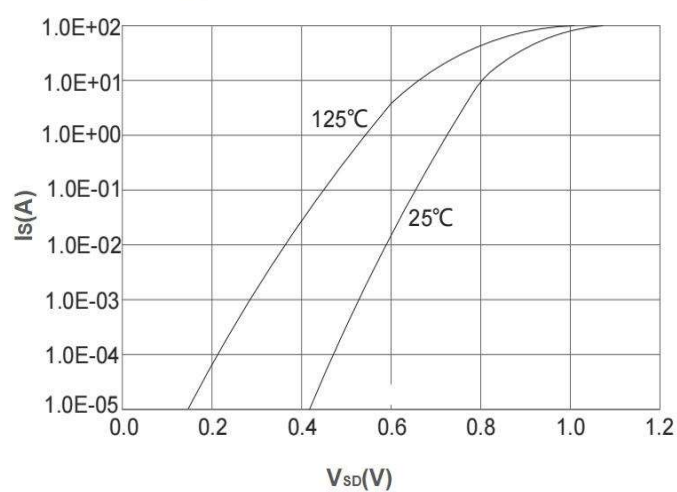


Figure 5: Gate Charge Characteristics

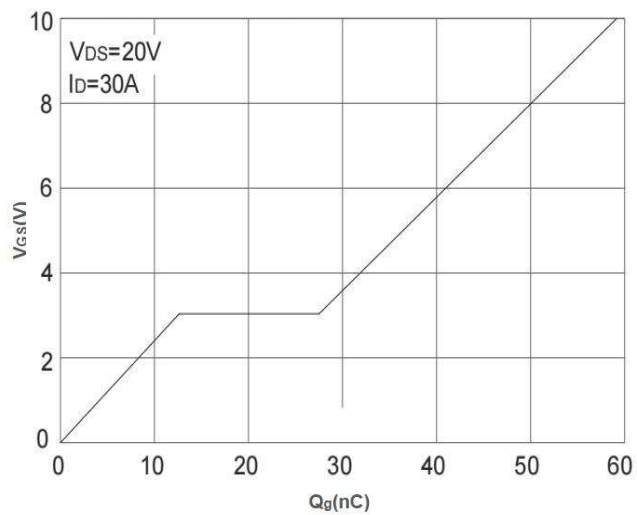
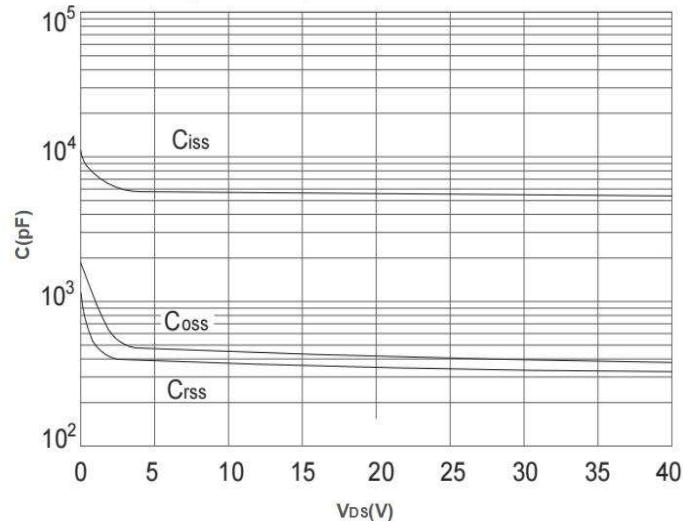


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

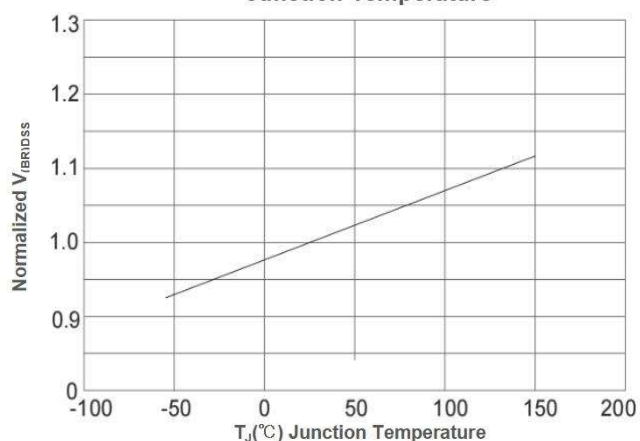


Figure 8: Normalized on Resistance vs. Junction Temperature

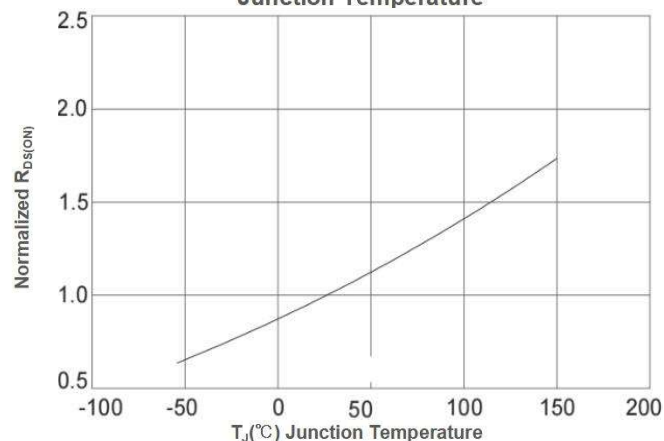


Figure 9: Maximum Safe Operating Area

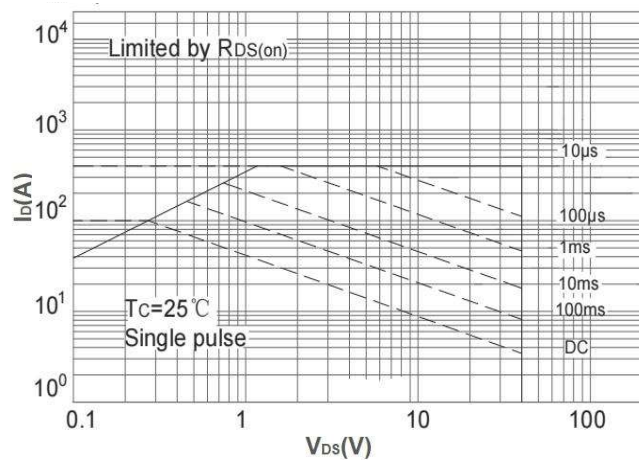


Figure 10: Maximum Continuous Drian Current vs. Case Temperature

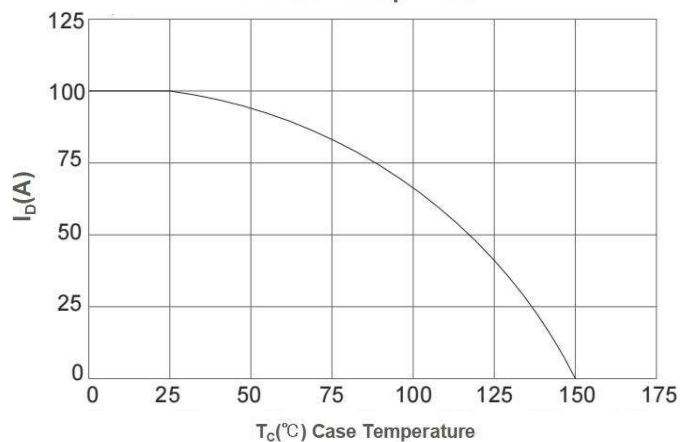


Figure 11: Normalized Maximum Transient Thermal Impedance

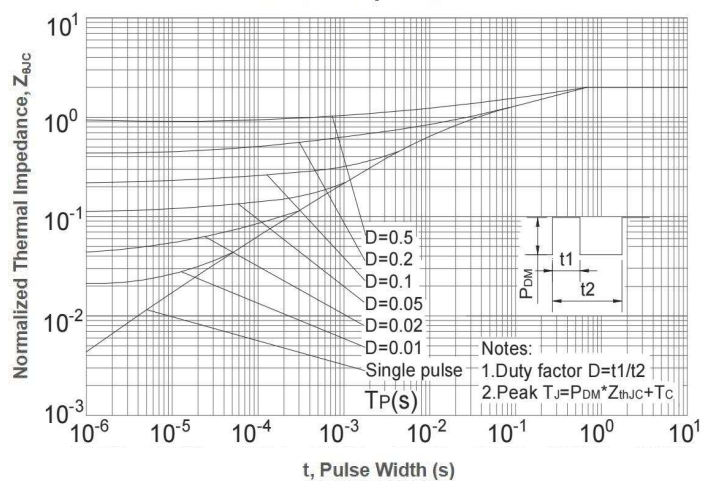
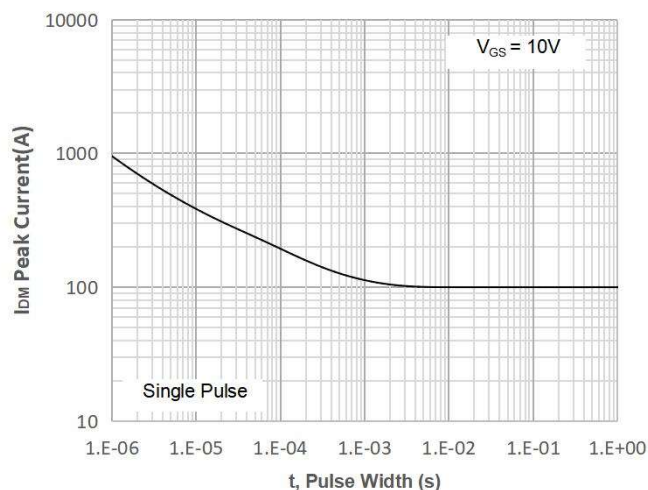


Figure 12: Peak Current Capacity



Test Circuit

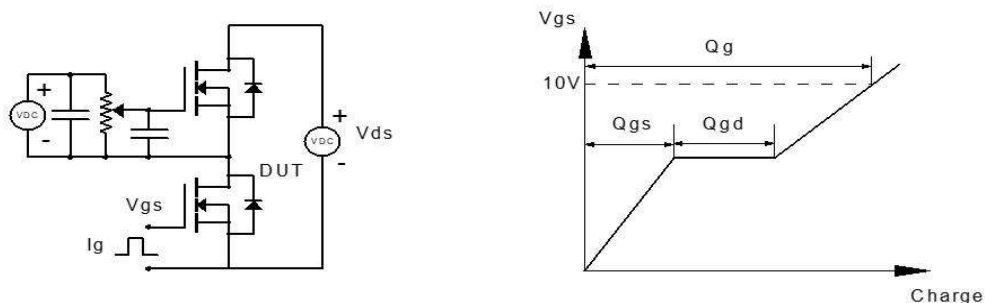


Figure 1: Gate Charge Test Circuit & Waveform

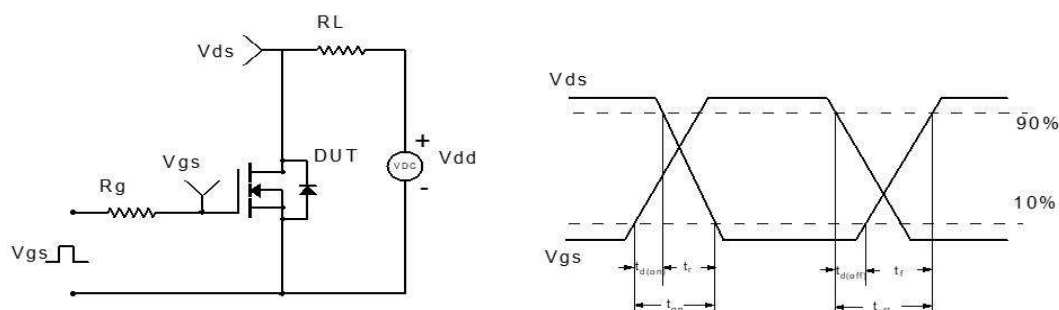


Figure 2: Resistive Switching Test Circuit & Waveform

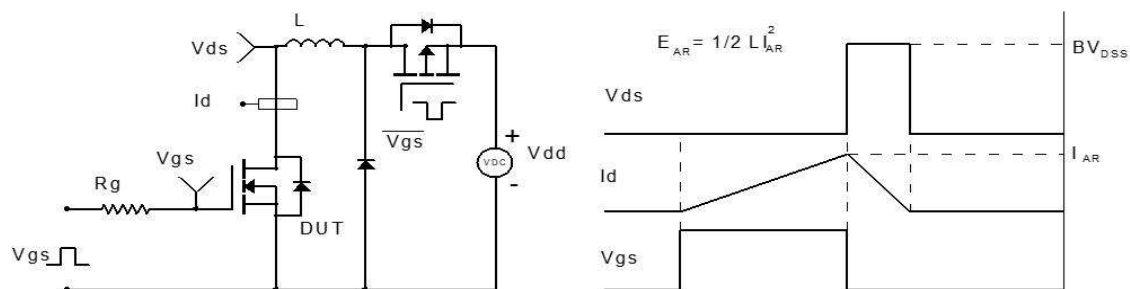


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

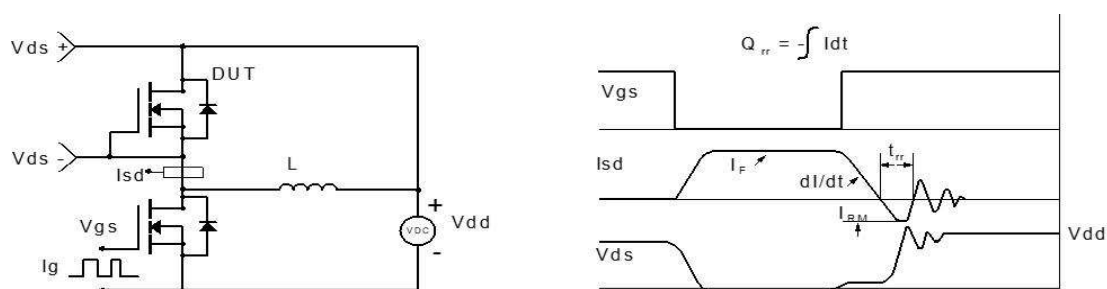
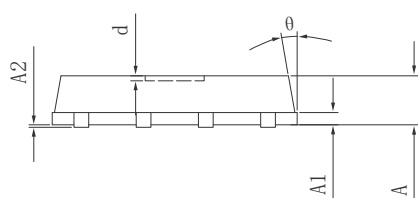
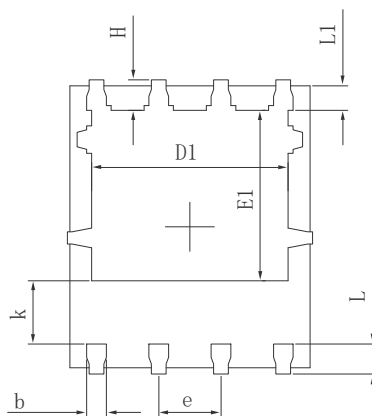
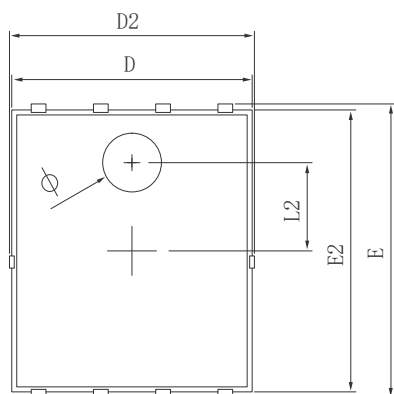
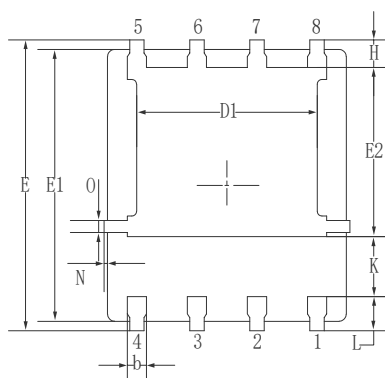
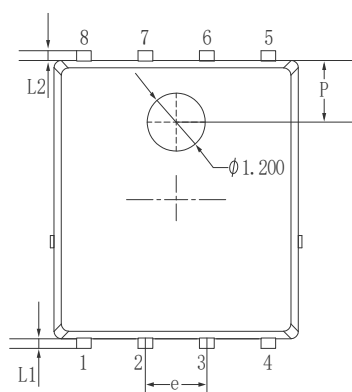


Figure 4: Diode Recovery Test Circuit & Waveform

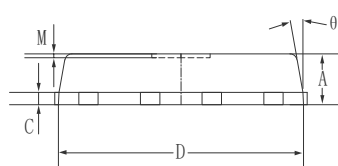
Dimensions (PDFN5*6)



SYMBOL	MILLIMETER		
	MIN.	TYP.	MAX.
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0~0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
Φ	1.100	1.200	1.300
d			0.100



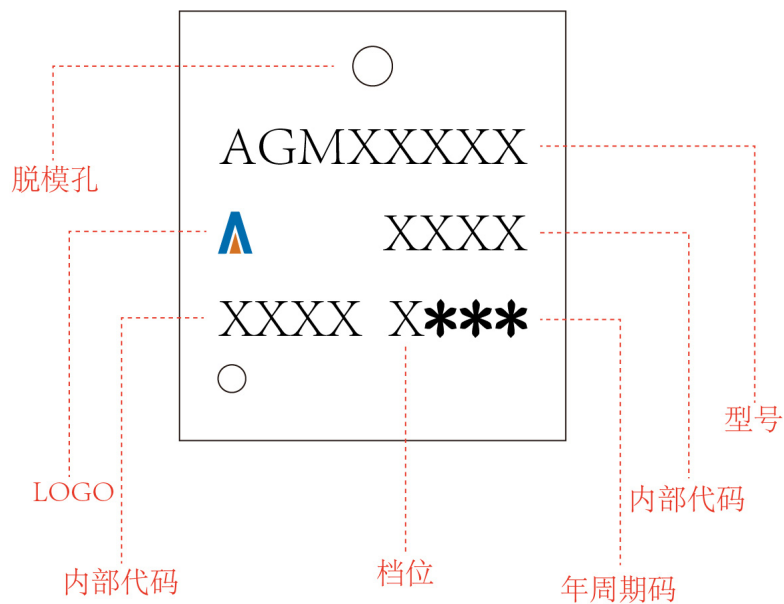
SYMBOL	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1	3.72	3.82	3.92
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		



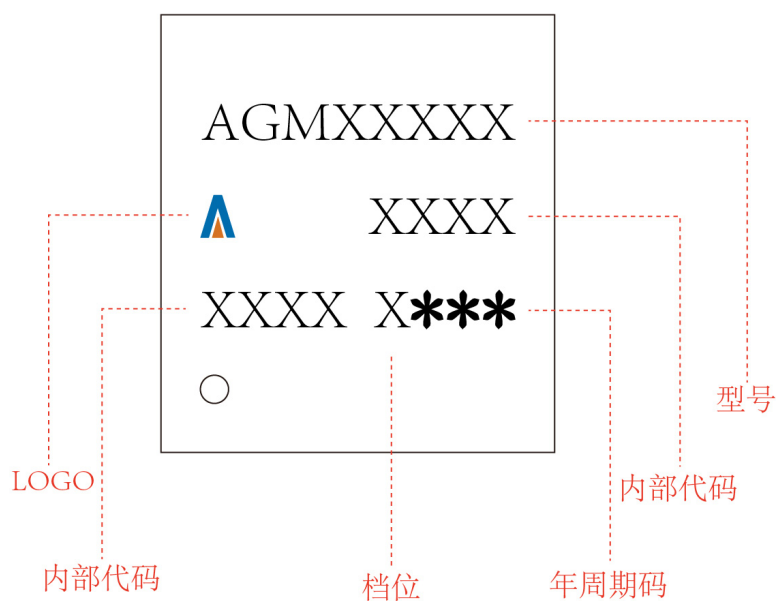
PDFN5*6

Marking Instructions:

Model1:



Model2:



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